# UNISONIC TECHNOLOGIES CO., LTD

# UTG6N65-S

**Preliminary** 

### Insulated Gate Bipolar Transistor

# 650V TRENCH GATE FIELD-STOP IGBT

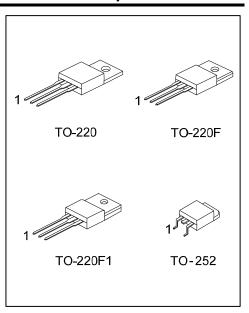
#### ■ DESCRIPTION

The UTC **UTG6N65-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

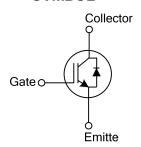
The UTC  ${\bf UTG6N65-S}$  is suitable for the resonant or soft switching applications.

#### **■ FEATURES**

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage:  $V_{CE(SAT).Typ.}=1.47V$  @  $I_C=6.0A$ ,  $V_{GE}=15V$  ( $T_C=25^{\circ}C$ )



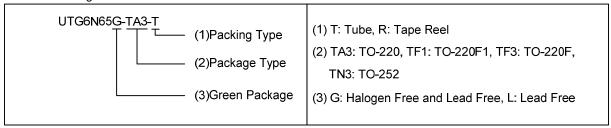
#### ■ SYMBOL



#### ORDERING INFORMATION

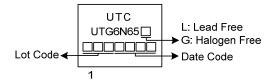
Ordering Number		Deelsene	Pin Assignment			Da akin n	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG6N65L-TA3-T	UTG6N65G-TA3-T	TO-220	G	С	Е	Tube	
UTG6N65L-TF1-T	UTG6N65G-TF1-T	TO-220F1	G	С	Е	Tube	
UTG6N65L-TF3-T	UTG6N65G-TF3-T	TO-220F	G	С	Е	Tube	
UTG6N65L-TN3-R	UTG6N65G-TN3-R	TO-252	G	С	Е	Tape Reel	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



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### **■** MARKING



#### ■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	650	V
Gate-Emitter Voltage			±20	V
Transient Gate-emitter voltage (tp < 5 ms)		V <sub>GES</sub>	±25	V
Continuous Collector Current	T <sub>C</sub> =25°C	Ic	12	Α
	T <sub>C</sub> =100°C		6	Α
Collector Current Pulsed (Note 1)		I <sub>CM</sub>	24	Α
Diode Forward Current	T <sub>C</sub> =25°C		12	Α
	T <sub>C</sub> =100°C	l <sub>F</sub>	6	Α
Short Circuit Withstand Time $V_{GE} = 15V$ , $V_{CC} \le 200V$ Allowed number of short circuits < 1000 Time between short circuits: $\ge 1.0s$ $T_{V,I} = 25^{\circ}C$		tsc	3	μs
Power Dissipation (T <sub>C</sub> =25°C)	TO-220		93	W
	TO-220F TO-220F1	P <sub>D</sub>	30	W
	TO-252		39	W
Operating Junction Temperature		TJ	-40 ~ +175	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +175	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

#### **■ THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Case	TO-220		1.34	°C/W
	TO-220F TO-220F1	θις	4.167	°C/W
	TO-252		3.205 (Note)	°C/W

Note: Device mounted on FR-4 substrate Pc board, 2oz copper, with 1inch square copper plate.

<sup>2.</sup> Pulse width limited by maximum junction temperature.

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS			TYP	MAX	UNIT
Off Characteristics							
Collector-Emitter Breakdown Voltage	BVces			650			V
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =650V, V <sub>GE</sub> =0V				5	μA
G-E Leakage Current	Iges	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V				±100	nΑ
On Characteristics		_				ā.	
Gate to Emitter Threshold Voltage	V <sub>GE(TH)</sub>	I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>		4.0		6.5	V
Collector to Emitter Saturation Voltage	V <sub>CE</sub> (SAT)	I <sub>C</sub> =6.0A, V <sub>GE</sub> =15V	T <sub>C</sub> =25°C T <sub>C</sub> =125°C		1.47 1.9	2.1	V
Dynamic Characteristics	I.		1.0 .=0 0			1	
Input Capacitance	CIES	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz			598		pF
Output Capacitance	Coes				37.8		pF
Reverse Transfer Capacitance	Cres			10.7		pF	
Switching Characteristics							
Total Gate Charge	Q <sub>G</sub>	V <sub>CE</sub> =520V, I <sub>C</sub> =6.0A, V <sub>GE</sub> =15V			49.4		nC
Gate-Emitter Charge	Q <sub>GE</sub>				14.3		nC
Gate-Collector Charge	Q <sub>GC</sub>				21.9		nC
Turn-On Delay Time	t <sub>DON)</sub>				15		ns
Rise Time	t <sub>R</sub>				19		ns
Turn-Off Delay Time	t <sub>DOFF)</sub>	V <sub>CC</sub> =400V, I <sub>C</sub> =6.0A, R <sub>G</sub> =5Ω, V <sub>GE</sub> =0~15V, L=1000μH			39		ns
Fall Time	t <sub>F</sub>				290		ns
Turn-On Switching Loss	Eon				0.154		mJ
Turn-Off Switching Loss	E <sub>OFF</sub>			0.147		mJ	
SOURCE- DRAIN DIODE RATINGS AN	D CHARACTE	ERISTICS					
Forward Voltage Drop	VF	I <sub>F</sub> =6.0A			1.6	3.0	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =6.0A, dI/dt=100A/μS,			43.8		ns
Reverse Recovery Charge	Qrr	V <sub>CC</sub> =400V			3.8		nC

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